

Takuya Kawazu

List of Publications by Year in descending order

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papers

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1307594

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36
times ranked

195
citing authors

#	ARTICLE	IF	CITATIONS
1	Synchronously wired infrared antennas for resonant single-quantum-well photodetection up to room temperature. <i>Nature Communications</i> , 2020, 11, 565.	12.8	40
2	Systematic studies for improving device performance of quantum well infrared stripe photodetectors. <i>Nanophotonics</i> , 2020, 9, 3373-3384.	6.0	10
3	Near-field resonant photon sorting applied: dual-band metasurface quantum well infrared photodetectors for gas sensing. <i>Nanophotonics</i> , 2020, 9, 4775-4784.	6.0	13
4	Enhancement of infrared photo-responses of the Schottky gate region of an n-AlGaAs/GaAs heterojunction FET by a second light illumination. <i>Japanese Journal of Applied Physics</i> , 2020, 59, 124003.	1.5	0
5	Metasurface Quantum Well Photodetectors with Broadened Photoresponse Using a Patchwork of Cavities within a Subwavelength Period. , 2020, , .		1
6	Valence Band Mixing in GaAs/AlGaAs Quantum Wells Adjacent to Self-Assembled InAlAs Antidots. <i>Journal of Nanomaterials</i> , 2019, 2019, 1-7.	2.7	3
7	Temperature dependence of Schottky photocurrent for local gate edge illumination in n-AlGaAs/GaAs/AlGaAs double-heterojunction field-effect transistor. <i>Japanese Journal of Applied Physics</i> , 2019, 58, S1B05.	1.5	0
8	Optical AND operation in n-AlGaAs/GaAs heterojunction field effect transistor. <i>Applied Physics Letters</i> , 2018, 112, .	3.3	5
9	Optical anisotropy of InGaAs quantum dot arrays aligned along multiaatomic steps on vicinal GaAs(111)B. <i>Journal of Applied Physics</i> , 2017, 122, 204304.	2.5	1
10	Photoinduced current in n-AlGaAs/GaAs heterojunction field-effect transistor driven by local illumination in edge regions of Schottky metal gate. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 04CG04.	1.5	3
11	Optical anisotropy of InGaAs quantum wire arrays on vicinal (111)B GaAs. <i>Journal of Applied Physics</i> , 2016, 120, 134309.	2.5	2
12	Excitation power dependence of photoluminescence spectra of GaSb type-II quantum dots in GaAs grown by droplet epitaxy. <i>AIP Advances</i> , 2016, 6, 045312.	1.3	2
13	Effects of Ga deposition rate and Sb flux on morphology of GaSb quantum dots formed on GaAs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 14, 1600109.	0.8	0
14	Electric states in laterally and vertically arrayed type-II quantum dots. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 04DJ01.	1.5	4
15	Lateral current generation in n-AlGaAs/GaAs heterojunction channels by Schottky-barrier gate illumination. <i>Applied Physics Letters</i> , 2015, 106, 022103.	3.3	4
16	GaAs/AlGaAs quantum wells with indirect-gap AlGaAs barriers for solar cell applications. <i>Applied Physics Letters</i> , 2014, 104, .	3.3	3
17	Growth of GaSb quantum dots on GaAs (111)A. <i>E-Journal of Surface Science and Nanotechnology</i> , 2014, 12, 304-306.	0.4	0
18	Growth of GaSb quantum dots on GaAs (311)A. <i>Journal of Crystal Growth</i> , 2013, 378, 475-479.	1.5	7

#	ARTICLE	IF	CITATIONS
19	Photo-induced current in n-AlGaAs/GaAs heterojunction channels driven by local illumination at the edge regions of Hall bar. Applied Physics Letters, 2013, 102, 252104.	3.3	2
20	Post-growth annealing of GaSb quantum dots in GaAs formed by droplet epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1505-1508.	0.8	3
21	Self-assembly of InAs ring complexes on InP substrates by droplet epitaxy. Journal of Applied Physics, 2012, 112, 063510.	2.5	14
22	Effects of interface grading on optical anisotropy in type-II quantum wells on high-index substrates. Physica E: Low-Dimensional Systems and Nanostructures, 2012, 44, 1351-1356.	2.7	3
23	Effects of Interface Grading on Electronic States in Columnar Type-II Quantum Dots. Japanese Journal of Applied Physics, 2012, 51, 02BJ09.	1.5	1
24	Growth of GaSb and InSb quantum dots on GaAs (311)A by droplet epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 275-277.	0.8	4
25	Effects of Interface Grading on Electronic States and Optical Transitions in GaSb Type-II Quantum Dots in GaAs. Japanese Journal of Applied Physics, 2011, 50, 04DJ06.	1.5	6
26	Optical anisotropy of GaSb type-II nanorods on vicinal (111)B GaAs. Applied Physics Letters, 2011, 99, 231901.	3.3	5
27	Effects of Interface Grading on Electronic States and Optical Transitions in GaSb Type-II Quantum Dots in GaAs. Japanese Journal of Applied Physics, 2011, 50, 04DJ06.	1.5	4
28	Thermal annealing of GaSb quantum dots in GaAs formed by droplet epitaxy. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2742-2744.	2.7	2
29	Anisotropic Transport of Electrons in a Novel FET Channel with Chains of InGaAs Nano-Islands Embedded along Quasi-Periodic Multi-Atomic Steps on Vicinal (111)B GaAs. , 2010, , .		2
30	Effects of Sb/As intermixing on optical properties of GaSb type-II quantum dots in GaAs grown by droplet epitaxy. Applied Physics Letters, 2010, 97, 261906.	3.3	22
31	EFFECTS OF ANTIMONY FLUX ON MORPHOLOGY AND PHOTOLUMINESCENCE SPECTRA OF GaSb QUANTUM DOTS FORMED ON GaAs BY DROPLET EPITAXY. Journal of Nonlinear Optical Physics and Materials, 2010, 19, 819-826.	1.8	6
32	Optical properties of GaSb/GaAs type-II quantum dots grown by droplet epitaxy. Applied Physics Letters, 2009, 94, 081911.	3.3	37
33	Growth of GaSb dots on GaAs(100) by droplet epitaxy. Physica Status Solidi (B): Basic Research, 2009, 246, 733-735.	1.5	16
34	Magneto-capacitance study of an n-AlGaAs/GaAs heterojunction supporting a sizable dc current. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2879-2881.	0.8	0
35	Electron scatterings in selectively doped n-AlGaAs/GaAs heterojunctions with high density self-assembled InAlAs antidots. Applied Physics Letters, 2008, 93, 132116.	3.3	3